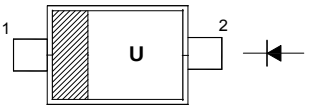
SILICON BAND SWITCHING DIODE

Applications

for band switching in VHF television tuners
and surface mount band switching circuits

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View
Marking Code: "**U**"
Simplified outline SOD-523 and symbol

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	35	V
Forward Current	I_F	100	mA
Junction Temperature	T_J	150	°C
Operating Temperature Range	T_{op}	- 55 to + 125	°C
Storage Temperature Range	T_{stg}	- 55 to + 150	°C

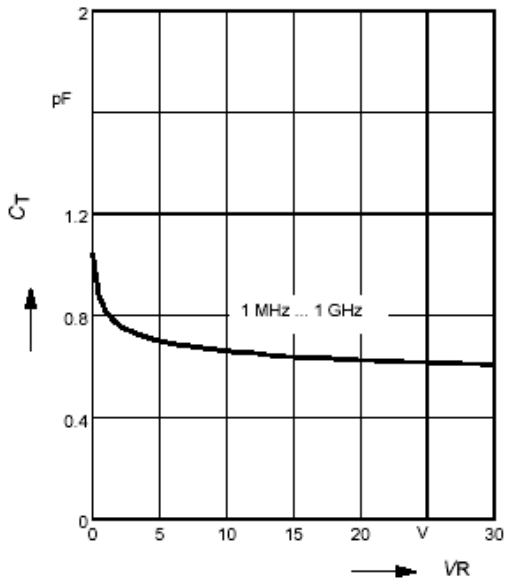
Characteristics at T_a = 25 °C

Parameter	Symbol	Min.	Typ.	Max.	Unit
Reverse Current at V_R = 20 V	I_R	-	-	20	nA
Forward Voltage at I_F = 100 mA	V_F	-	-	1	V
Diode Capacitance at V_R = 1 V, f = 1 MHz at V_R = 3 V, f = 1 MHz at V_R = 0 V, f = 100 MHz	C_T	0.65 0.6 -	- - 1	1.4 1.1 -	pF
Forward Resistance at I_F = 3 mA, f = 100 MHz at I_F = 10 mA, f = 100 MHz	r_f	- -	- -	0.7 0.5	Ω
Series Inductance	L_s	-	0.6	-	nH

BA892WT

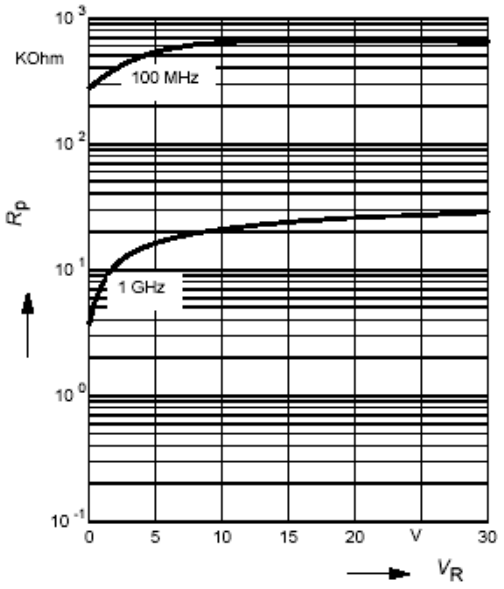
Diode capacitance $C_T = f(V_R)$

f = Parameter



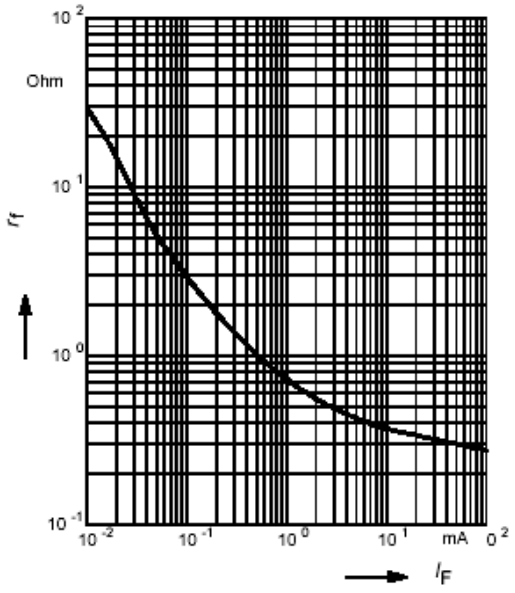
Reverse parallel resistance $R_P = f(V_R)$

f = Parameter



Forward resistance $r_f = f(I_F)$

f = 100MHz



Forward current $I_F = f(V_F)$

T_A = Parameter